

Analog Circuits 1

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Low Power Loss IGBT Driver Circuit Using Current Drive

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- Research Background and Objective
- IGBT Evaluation Circuit
- IGBT Current Drive Simulation
 - Current Gate Driver Circuit
 - Simulation Results
- Conclusion and Challenges





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Research Background

IGBTs have advantages of both MOSFETs and bipolar transistors

Used in wide range of applications as power semiconductor devices



Development of IGBT and its driver circuit is important





IGBT and Driver Circuit

IGBT (Insulated Gate Bipolar Transistor)



Input part is **MOSFET** Output part is bipolar transistor

Advantages

- Fast operating speed
- Large current amplification factor (~1.2kA)
- High withstand voltage (~3.3kV)

Large gate capacitance Driver circuit is difficult



Objective

IGBT circuit

- Parasitic capacitance and tail current cause switching loss
 - Parasitic inductance causes
 excessive overshoot

Reduction of switching loss and excessive overshoot by current drive control of IGBT



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Voltage-Driven IGBT Evaluation Circuit (1/2)





Voltage-Driven IGBT Evaluation Circuit (2/2)





Overshoot and Switching Loss during Turn-off





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Current Gate Driver Circuit (1/2)





Current Gate Driver Circuit (2/2)





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IGBT Turn-off Characteristics





Control of Gate Voltage by Gate Current (Step1)

Step1

V_g : Saturation voltage to Miller voltage

No effects on switching loss and overshoot





Control of Gate Voltage by Gate Current (Step2)

Step2

 V_g : Miller period of IGBT

Trade-off between switching loss and slew rate

Switching loss can be reduced





Control of Gate Voltage by Gate Current (Step3)

Step3

V_g : Miller voltage to threshold voltage

Trade-off between switching loss and overshoot







Control of Gate Voltage by Gate Current (Step4)

Step4

 V_g : Threshold voltage to $\boldsymbol{0}$

I_g : Uncontrollable due to I-V characteristics of MOSFETs

No effects on switching loss and overshoot





Comparison with Voltage Drive

Switching Loss : -30%, Overshoot : -28%





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Conclusion

- Proposal of current drive circuit to control gate voltage of IGBT
- Current drive circuit draws different value of current at each 4-step operating region
- Simulation verification: During turn-off, reduction of switching loss (-30%), overshoot (-28%) compared to conventional voltage drive



Challenges

- Improve the current drive circuit
 - Adapt to change in supply voltage during turn-off and supply charge during turn-on
 - Current drive will simplify the circuit to adapt to various changes



Thank you for your attention



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